

D6-4-808-1000



Application

Laser Projector
Measuring equipment

Property

Wavelength $\lambda = 808 \text{ nm}$
Output Power = 1000mW
Package Type = $\varnothing 5.6\text{mm}$

Introduction

Egismos currently markets AlGaAs infrared laser diodes in the 780nm ~ 1550nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers, blue laser DVD, laser barcode scanners, diode laser equipments, medical instruments and aerospace applications.

Red Laser Diode Key features

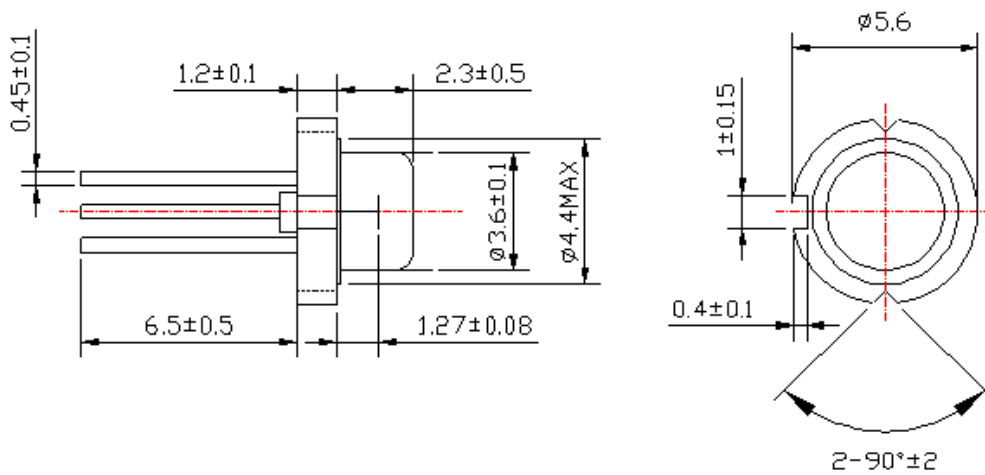
Absolute Maximum Rating at $T_c=25^\circ\text{C}$

Items		Symbols	Values	Unit
Operating Current power		P_o	1000	mW
Reverse Voltage	LD	V_R	2	V
Operating Temperature		T_{case}	-10~+40	$^\circ\text{C}$
Storage Temperature		T_s	-10~+85	$^\circ\text{C}$

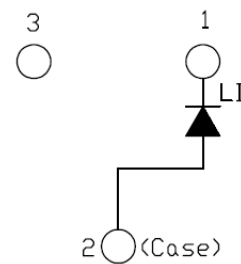
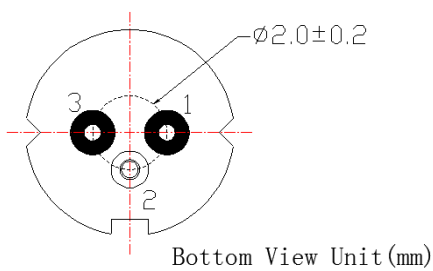
Electrical and Optical Characteristics at Tc=25°C

Item	Symbols	Min	Typ.	Max.	Unit	Condition
Threshold Current	I_{th}	-	220		mA	-
Operating Current	I_{op}	-	1200	1500	mA	Po=500mW
Operating Voltage	V_{op}	-	2.0	2.2	V	Po=500mW
Peak Wavelength	λ_p	803	808	813	nm	Po=500mW
Beam Divergence (FWHM)	θ_r		8		deg	Po=500mW
Beam Divergence (FWHM)	θ_{\pm}		28		deg	Po=500mW
Monitor Current	I_m		0.9		mA	Po=500mW

Package Drawing



ELECTRICAL CONNECTION



Specifications are subject to change without notice.

